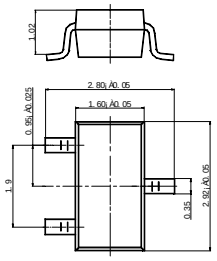
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23-3L Plastic-Encapsulate Transistors

SOT-23-3L

1. BASE
2. EMITTER
3. COLLECTOR



MMBTA44 TRANSISTOR (NPN)

FEATURES

Power dissipation

$P_{CM:}$ 0.35 W (Tamb=25℃)

Collector current

$I_{CM:}$ 0.2 A

Collector-base voltage

$V_{(BR)CBO}$: 400 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic= 100μA, I_E=0	400			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C= 1mA , I_B=0	400			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E=100μA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=400V, I_E=0			0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}=400V			5	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 4V, I_C=0			0.1	μA
DC current gain	$H_{FE(1)}$	V_{CE}=10V, I_C=10 mA	80		300	
	$H_{FE(2)}$	V_{CE}=10V, I_C=1mA	70			
	$H_{FE(3)}$	V_{CE}=10V, I_C=100 mA	60			
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=10 mA, I_B=1mA			0.2	V
	V_{CE}(sat)	I_C=50 mA, I_B=5mA			0.3	V
Base-emitter sataration voltage	V_{BE}(sat)	I_C=10 mA, I_B= 1 mA			0.75	V
Transition frequency	f_T	V_{CE}=20V, I_C=10mA f =30MHz	50			MHz

MARKING	**3D**